

Notice of References Cited			Application/Control No.	Applicant(s)/Patent Under Reexamination SAKAI ET AL.	
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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
	C	US-			
	D	US-			
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NON-PATENT DOCUMENTS

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	V	H.J. Osten et al., "Epitaxial Praseodymium Oxide: A New High-k Dielectric", November 2001, Extended Abstracts of International Workshop on Gate Insulators, pages 100-106.
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	X	H.J. Osten et al., "High-k Dielectrics with Ultra-low Leakage Current Based on Praseodymium Oxide", December 2000, International Electron Devices meeting. IEDM Technical Digest, pages 653-656.

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.